Notice of Allowability	Application No.	Applicant(s)	
	10/072,362	FU, KUAN-YU	
	Examiner	Art Unit	
	Shouxiang Hu	2811	
	Grounding Flu	2011	 -
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	olication. If not included will be mailed in due course. THI	S ative
1. This communication is responsive to <u>10/31/06</u> .			
2. The allowed claim(s) is/are 10-12.			
 3.	been received.	0/202 146	
3. Copies of the certified copies of the priority do	• • • • • • • • • • • • • • • • • • • •		۵
International Bureau (PCT Rule 17.2(a)).	differents have been received in this i	adional stage application from the	,
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below: Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a reply of this application.	complying with the requirements	
4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	itted. Note the attached EXAMINER'es reason(s) why the oath or declara	S AMENDMENT or NOTICE OF tion is deficient.	
 5. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1) 	son's Patent Drawing Review (PTO-son's Patent Drawing Review (PTO-son's Patent (PTO-son's PTO-son's Patent (PTO-son's Patent (PTO-son's Patent (PTO-son's Patent (PTO-son's Patent (PTO-son's Patent (PTO-son's PTO-son's Patent (PTO-son's PTO-son's PTO-son's Patent (PTO-son's PTO-son's PT	Office action of	
each sheet. Replacement sheet(s) should be labeled as such in t			
6. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT			
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Attachment(s)			
1. ☑ Notice of References Cited (PTO-892)	5. Notice of Informal P		
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ⊠ Interview Summary Paper No./Mail Dat	•	
 Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 	7. Examiner's Amendr		
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. Examiner's Stateme	ent of Reasons for Allowance	
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EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Jiawei Huang (RN: 43,330) on January 11, 2007.

The application has been amended as follows:

IN THE CLAIMS

In claim 10, replace the last paragraph in the claim (i.e., lines 1-6 on Page 3 of 8 in the 10-31-2006 amendment, which states: "a first shallow doped region within the substrate disposed at an upper comer adjacent to the first conductive vertical portion and a second shallow doped region disposed at an upper comer adjacent to the second conductive vertical portion of the electrode; and a first deep source region extending from the first shallow doped region and a second deep drain region extending from the second shallow doped region are disposed in a region within the substrate deeper than the first and second trenches.") With:

--a pair of shallow doped regions within the substrate disposed adjacent to and on two opposite sides of each of the first and second conductive vertical portions and the conductive horizontal portion; and a pair of deep doped regions extending respectively from the first pair of shallow doped regions to regions within the substrate deeper than the first and second trenches, Application/Control Number: 10/072,362

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wherein the pair of shallow doped regions form shallow source/drain regions with

a shallow channel region therebetween below the conductive horizontal portion; and,

wherein the pair of deep doped regions form deep source/drain regions with two

deep channel regions therebetween below the first and second trenches, respectively.--

Claims 13-15 (cancelled).

Allowable Subject Matter

Claims 10-12 are allowed.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. References A is cited as being related to a trench-gated

MOSFET structure.

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Shouxiang Hu whose telephone number is 571-272-

1654. The examiner can normally be reached on Monday through Friday, 8:30 AM to

5:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Richard T. Elms can be reached on 571-272-1869. The fax phone number

for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

SH January 12, 2007

SHOUXIANG HU